

ABSTRACT OF THE DISCLOSURE

A method of manufacturing an electronic device includes the steps of: (a) preparing a (001) oriented ReO_3 layer; and (b) forming a (001) oriented oxide ferroelectric layer having a perovskite structure on the ReO_3 layer. Preferably, the
5 step (a) includes the steps of: (a-1) preparing a (001) oriented MgO layer; and (a-2) forming a (001) oriented ReO_3 layer on the MgO layer. An electronic device capable of obtaining a ferroelectric layer of a large polarization and a method of manufacturing the same are provided.